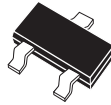




CMPD2003 **CMPD2004**
CMPD2003A **CMPD2004A**
CMPD2003C **CMPD2004C**
CMPD2003S **CMPD2004S**

**SURFACE MOUNT
 HIGH VOLTAGE
 SILICON SWITCHING DIODE**



SOT-23 CASE

Central™

Semiconductor Corp.

DESCRIPTION:

The Central Semiconductor CMPD2003, CMPD2003A, CMPD2003C, CMPD2003S, CMPD2004, CMPD2004A, CMPD2004C and CMPD2004S types are silicon switching diodes manufactured by the epitaxial planar process, designed for applications requiring high voltage capability.

The following configurations are available:

CMPD2003	SINGLE
CMPD2003A	DUAL, COMMON ANODE
CMPD2003C	DUAL, COMMON CATHODE
CMPD2003S	DUAL, IN SERIES
CMPD2004	SINGLE
CMPD2004A	DUAL, COMMON ANODE
CMPD2004C	DUAL, COMMON CATHODE
CMPD2004S	DUAL, IN SERIES

MARKING CODE: A82
MARKING CODE: 8A2
MARKING CODE: C3C
MARKING CODE: C3S
MARKING CODE: D53
MARKING CODE: DB8
MARKING CODE: DB7
MARKING CODE: DB6

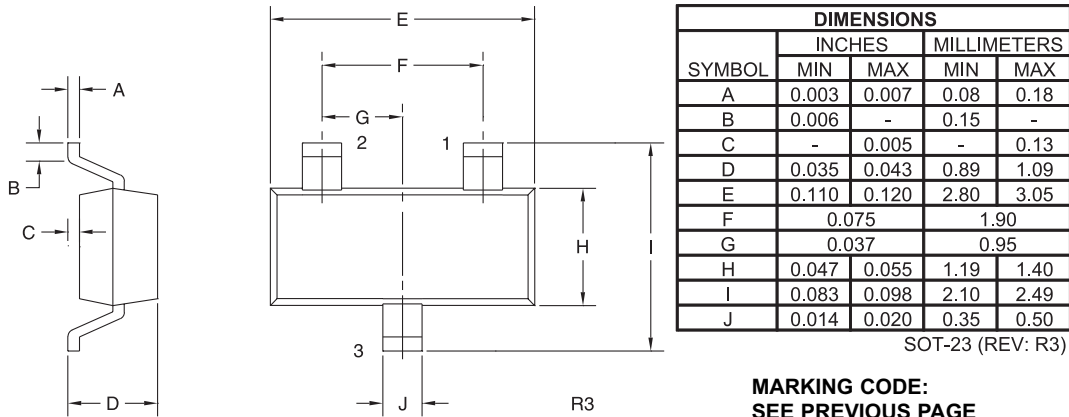
MAXIMUM RATINGS: (T _A =25°C)	SYMBOL	CMPD2003	CMPD2004	UNITS
		CMPD2003A CMPD2003C CMPD2003S	CMPD2004A CMPD2004C CMPD2004S	
Continuous Reverse Voltage	V _R	200	240	V
Peak Repetitive Reverse Voltage	V _{RRM}	250	300	V
Peak Repetitive Reverse Current	I _O	200	200	mA
Continuous Forward Current	I _F	250	225	mA
Peak Repetitive Forward Current	I _{FRM}		625	mA
Forward Surge Current, tp=1.0µs	I _{FSM}		4.0	A
Forward Surge Current, tp=1.0s	I _{FSM}		1.0	A
Power Dissipation	P _D		350	mW
Operating and Storage Junction Temperature	T _J , T _{stg}		-65 to +150	°C
Thermal Resistance	θ _{JA}		357	°C/W

**SURFACE MOUNT
 HIGH VOLTAGE
 SILICON SWITCHING DIODE**

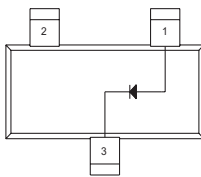
ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	CMPD2003		CMPD2004		UNITS
		MIN	MAX	MIN	MAX	
BV_R	$I_R=100\mu\text{A}$	250	-	300	-	V
I_R	$V_R=200\text{V}$	-	100	-	-	nA
I_R	$V_R=200\text{V}, T_A=150^\circ\text{C}$	-	100	-	-	μA
I_R	$V_R=240\text{V}$	-	-	-	100	nA
I_R	$V_R=240\text{V}, T_A=150^\circ\text{C}$	-	-	-	100	μA
V_F	$I_F=100\text{mA}$	-	1.0	-	1.0	V
V_F	$I_F=200\text{mA}$	-	1.25	-	-	V
C_T	$V_R=0\text{V}, f=1.0\text{ MHz}$	-	5.0	-	5.0	pF
t_{tr}	$I_R=I_F=30\text{mA}, R_L=100\Omega, \text{Rec. to } 3.0\text{mA}$	-	50	-	50	ns

SOT-23 CASE - MECHANICAL OUTLINE



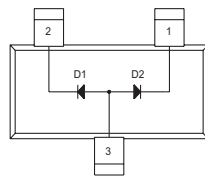
**MARKING CODE:
 SEE PREVIOUS PAGE**



LEAD CODE:

**CMPD2003
 CMPD2004**

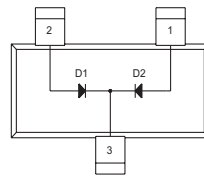
- 1) Anode
- 2) No Connection
- 3) Cathode



LEAD CODE:

**CMPD2003A
 CMPD2004A**

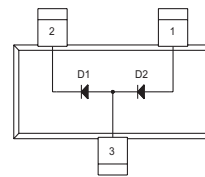
- 1) Cathode D2
- 2) Cathode D1
- 3) Anode D1, Anode D2



LEAD CODE:

**CMPD2003C
 CMPD2004C**

- 1) Anode D2
- 2) Anode D1
- 3) Cathode D1, Cathode D2



LEAD CODE:

**CMPD2003S
 CMPD2004S**

- 1) Anode D2
- 2) Cathode D1
- 3) Anode D1, Cathode D2